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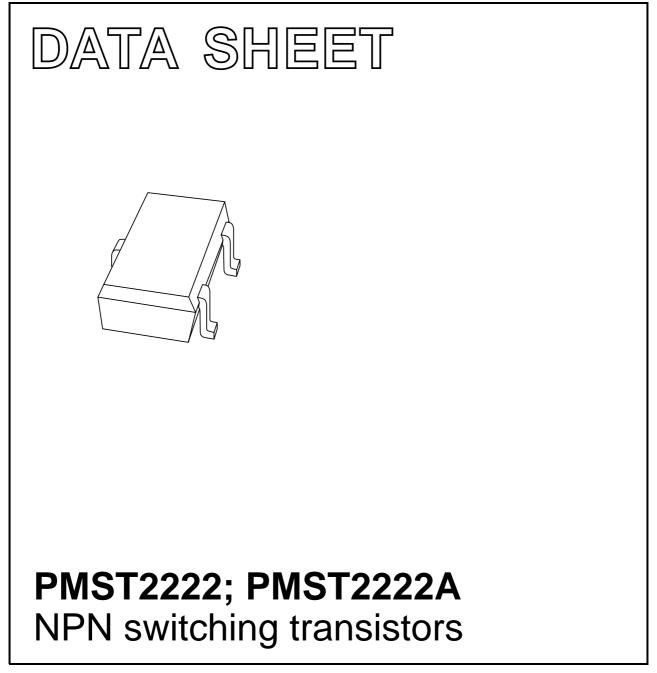
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Jul 14 1999 Apr 22



FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

• High-speed switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT323 plastic package. PNP complement: PMST2907A.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST2222	*1B
PMST2222A	*1P

Note

1. * = - : Made in Hong Kong.

* = t : Made in Malaysia.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	PMST2222		_	60	V
	PMST2222A		_	75	V
V _{CEO}	collector-emitter voltage	open base			
	PMST2222		_	30	V
	PMST2222A		_	40	V
V _{EBO}	emitter-base voltage	open collector			
	PMST2222		_	5	V
	PMST2222A		_	6	V
I _C	collector current (DC)		_	600	mA
I _{CM}	peak collector current		_	800	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C; note 1$	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		—	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

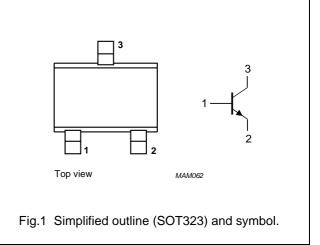
Note

1. Transistor mounted on an FR4 printed-circuit board.

PMST2222; PMST2222A

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



PMST2222; PMST2222A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

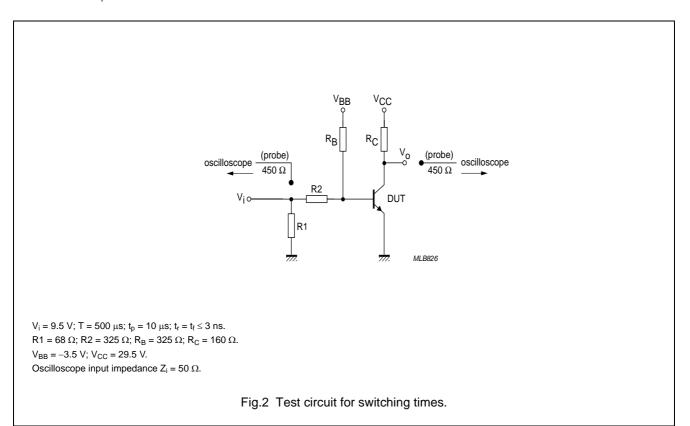
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 50 V	_	10	nA
	PMST2222	I _E = 0; V _{CB} = 50 V; T _j = 125 °C	_	10	μA
	collector cut-off current	I _E = 0; V _{CB} = 60 V	_	10	nA
	PMST2222A	I _E = 0; V _{CB} = 60 V; T _j = 125 °C	_	10	μA
I _{EBO}	collector cut-off current	I _C = 0; V _{EB} = 3 V	-	10	nA
h _{FE}	DC current gain	I _C = 0.1 mA; V _{CE} = 10 V	35	_	
		I _C = 1 mA; V _{CE} = 10 V	50	_	
		I _C = 10 mA; V _{CE} = 10 V	75	_	
		I_{C} = 10 mA; V_{CE} = 10 V; T_{amb} = -55 °C	35	_	
		I _C = 150 mA; V _{CE} = 1 V; note 1	50	_	
		I _C = 150 mA; V _{CE} = 10 V; note 1	100	300	
	DC current gain	I _C = 500 mA; V _{CE} = 10 V; note 1			
	PMST2222		30	_	
	PMST2222A		40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	400	mV
	PMST2222	$I_{C} = 500 \text{ mA}; I_{B} = 50 \text{ mA}; \text{ note } 1$	_	1.6	V
	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	300	mV
	PMST2222A	$I_{C} = 500 \text{ mA}; I_{B} = 50 \text{ mA}; \text{ note } 1$	_	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	_	1.3	V
	PMST2222	$I_{C} = 500 \text{ mA}; I_{B} = 50 \text{ mA}; \text{ note } 1$	_	2.6	V
	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; note 1	0.6	1.2	V
	PMST2222A	$I_{\rm C} = 500 \text{ mA}; I_{\rm B} = 50 \text{ mA}; \text{ note } 1$	_	2	V
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	-	8	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$			
	PMST2222		_	30	pF
	PMST2222A		_	25	pF
f _T	transition frequency	I _C = 20 mA; V _{CE} = 20 V; f = 100 MHz			1
	PMST2222		250	-	MHz
	PMST2222A		300	_	MHz

PMST2222; PMST2222A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
F	noise figure	$I_C = 200 \ \mu$ A; V _{CE} = 5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz	-	4	dB
Switching t	imes (between 10% and 90% levels); (see Fig.2)			
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	_	35	ns
t _d	delay time	I _{Boff} = -15 mA	_	15	ns
t _r	rise time		_	20	ns
t _{off}	turn-off time		_	250	ns
t _s	storage time		_	200	ns
t _f	fall time		-	60	ns

Note

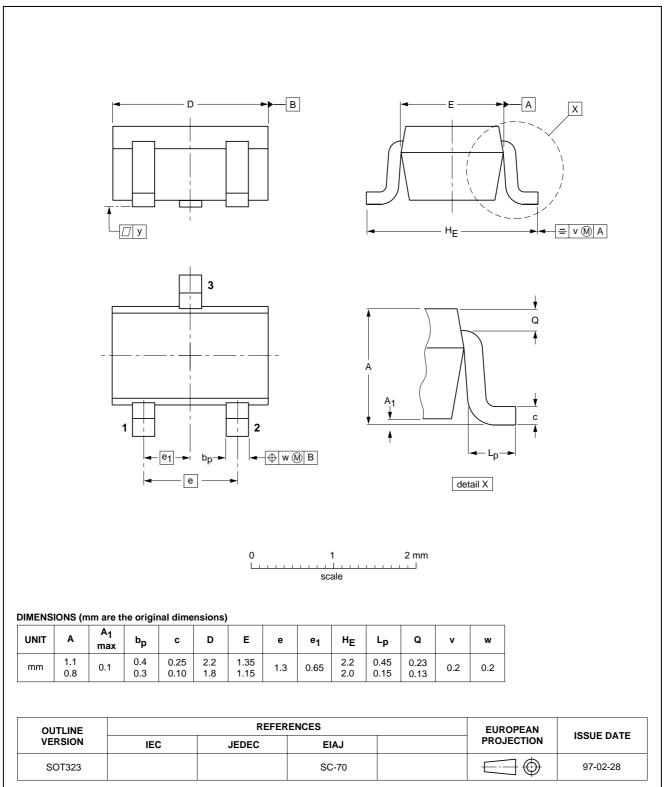
1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



PMST2222; PMST2222A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads



PMST2222; PMST2222A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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Contact information

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